

# N-channel SiC power MOSFET

$V_{\mathrm{DSS}}$	1700V
$R_{DS(on)}(Typ.)$	750m $\Omega$
I <sub>D</sub>	6A
P <sub>D</sub>	57W

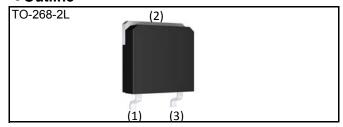
## Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Long creepage distance with no center lead
- 4) Simple to drive
- 5) Pb-free lead plating; RoHS compliant

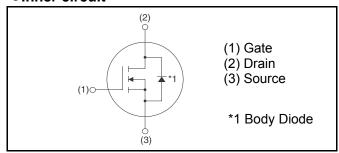
# Application

- Auxilialy power supplies
- Switch mode power supplies

### Outline



## •Inner circuit



Packaging specifications

	Packing	Embossed tape
	Reel size (mm)	330
Typo	Tape width (mm)	24
Туре	Basic ordering unit (pcs)	400
	Taping code	TB
	Marking	SCT2750NY

# ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V <sub>DSS</sub>	1700	V
Continuous drain current	T <sub>c</sub> = 25°C	l <sub>D</sub> *1	5.9	А
Continuous drain current	T <sub>c</sub> = 100°C	l <sub>D</sub> *1	4	А
Pulsed drain current		I <sub>D,pulse</sub> *2	14	А
Gate - Source voltage (DC)		V <sub>GSS</sub>	-6 to 22	V
Gate - Source surge voltage (t <sub>surge</sub> <300nsec)		V <sub>GSS_surge</sub> *3	–10 to 26	V
Power dissipation (T <sub>c</sub> = 25°C)		P <sub>D</sub>	57	W
Junction temperature		Tj	175	°C
Range of storage temperature		T <sub>stg</sub>	-55 to +175	°C

## ●Thermal resistance

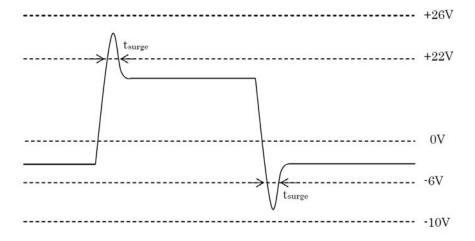
Parameter	Symbol	Values			Unit
r arameter	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	$R_{thJC}$	-	2.04	2.65	°C/W

## ●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	1700	-	1	V
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = 1700V, V_{GS} = 0V$ $T_{j} = 25^{\circ}C$ $T_{j} = 150^{\circ}C$		0.1 0.2	10	μΑ
Gate - Source leakage current	I <sub>GSS+</sub>	$V_{GS} = +22V, V_{DS} = 0V$	-	1	100	nA
Gate - Source leakage current	I <sub>GSS-</sub>	$V_{GS} = -6V, V_{DS} = 0V$	-	ı	-100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 0.63 \text{mA}$	1.6	2.8	4.0	V

<sup>\*1</sup> Limited only by maximum temperature allowed.

## \*3 Example of acceptable Vgs waveform



\*4 Pulsed

<sup>\*2</sup> PW  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

Darameter	Cumbal	Symbol Conditions		Values		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
		$V_{GS} = 18V, I_D = 1.7A$				
Static drain - source on - state resistance	R <sub>DS(on)</sub> *4	T <sub>j</sub> = 25°C	-	750	975	mΩ
		T <sub>j</sub> = 125°C	-	1088	-	
Gate input resistance	$R_{G}$	f = 1MHz, open drain	-	49	-	Ω
Transconductance	g <sub>fs</sub> *4	$V_{DS} = 10V, I_D = 1.7A$	-	0.6	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	275	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 800V	-	19	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	7	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	$V_{GS} = 0V$ $V_{DS} = 0V$ to 800V	-	21	-	pF
Turn - on delay time	t <sub>d(on)</sub> *4	$V_{DD} = 500V, I_D = 1.7A$	-	19	-	
Rise time	t <sub>r</sub> *4	V <sub>GS</sub> = 18V/0V	-	24	-	20
Turn - off delay time	t <sub>d(off)</sub> *4	$R_L = 294\Omega$	-	41	-	ns
Fall time	t <sub>f</sub> *4	$R_G = 0\Omega$	-	63	-	
Turn - on switching loss	E <sub>on</sub> *4	$V_{DD} = 800V, I_{D} = 1.7A$ $V_{GS} = 18V/0V$	-	76	-	!
Turn - off switching loss	E <sub>off</sub> *4	$R_G = 0\Omega$ , L=2mH * $E_{on}$ includes diode reverse recovery	-	33	-	μJ

# ●Gate Charge characteristics (T<sub>a</sub> = 25°C)

Darameter	Cymahal	Conditions	Values			Linit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Total gate charge	Qg *4	V <sub>DD</sub> = 500V	-	17	-	
Gate - Source charge	Q <sub>gs</sub> *4	I <sub>D</sub> = 1.5A	-	5	-	nC
Gate - Drain charge	Q <sub>gd</sub> *4	V <sub>GS</sub> = 18V	-	6.5	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} = 500V, I_D = 1.5A$	-	11.0	-	V

# ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
raiainetei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l <sub>S</sub> *1	-T <sub>c</sub> = 25°C	-	-	5.9	А
Inverse diode direct current, pulsed	I <sub>SM</sub> *2		-	-	14	Α
Forward voltage	V <sub>SD</sub> *4	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.7A	-	4.3	-	V
Reverse recovery time	t <sub>rr</sub> *4		-	26	ı	ns
Reverse recovery charge	Q <sub>rr</sub> *4	I <sub>F</sub> = 1.7A, V <sub>R</sub> = 800V di/dt = 290A/μs	-	18	-	nC
Peak reverse recovery current	I <sub>rrm</sub> *4		-	1.3	-	Α

# ● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R <sub>th1</sub>	243m	
R <sub>th2</sub>	1529m	K/W
R <sub>th3</sub>	268m	

Symbol	Value	Unit
C <sub>th1</sub>	352µ	
C <sub>th2</sub>	1.57m	Ws/K
C <sub>th3</sub>	68.7m	

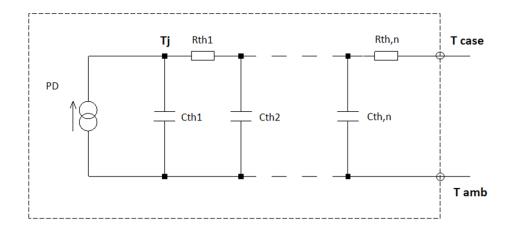
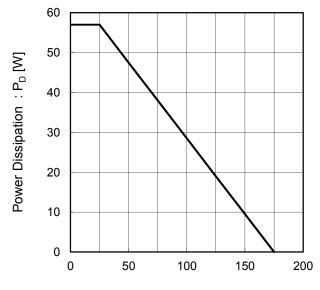
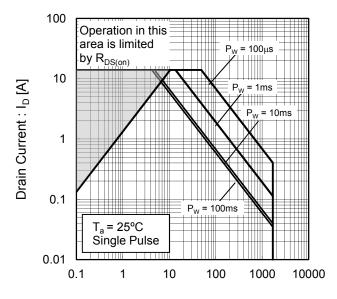


Fig.1 Power Dissipation Derating Curve

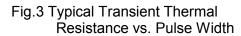


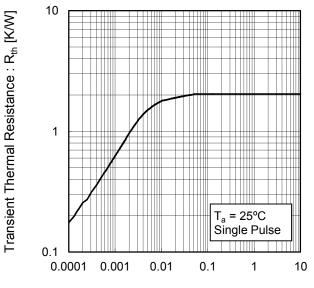
Junction Temperature : T<sub>i</sub> [°C]

Fig.2 Maximum Safe Operating Area



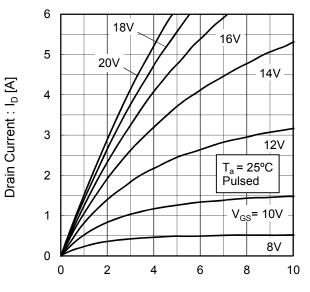
Drain - Source Voltage : V<sub>DS</sub> [V]





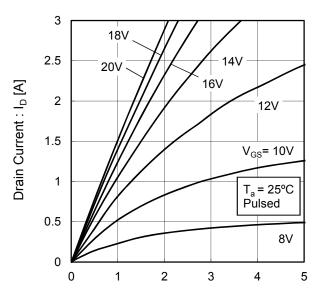
Pulse Width :  $P_W$  [s]

Fig.4 Typical Output Characteristics(I)

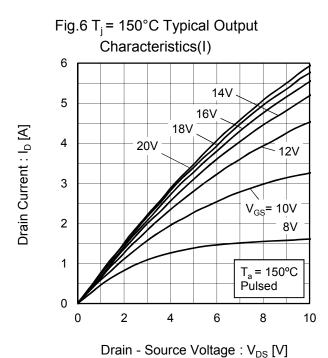


Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.5 Typical Output Characteristics(II)



Drain - Source Voltage : V<sub>DS</sub> [V]

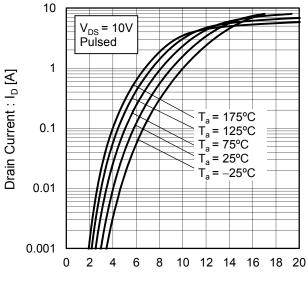


Drain Current : I<sub>D</sub> [A]

Fig.7 T<sub>i</sub> = 150°C Typical Output Characteristics(II) 3 3 14V 16V 18V 2 20V  $V_{GS}$ = 10V2 8V -1 1 T<sub>a</sub> = 150°C Pulsed 0 2 5 0 1 3

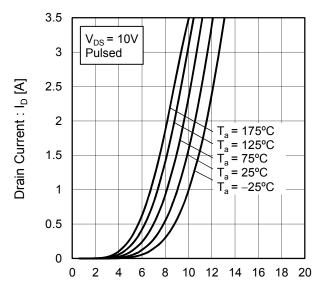
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.8 Typical Transfer Characteristics (I)



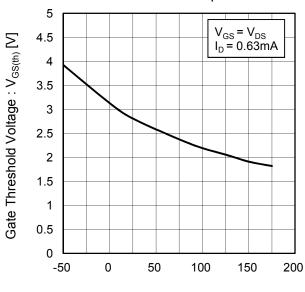
Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.9 Typical Transfer Characteristics (II)



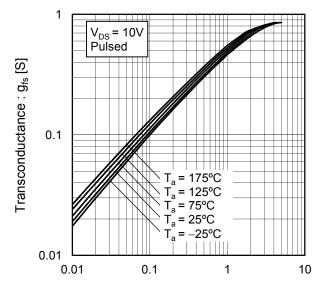
Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.10 Gate Threshold Voltage vs. Junction Temperature



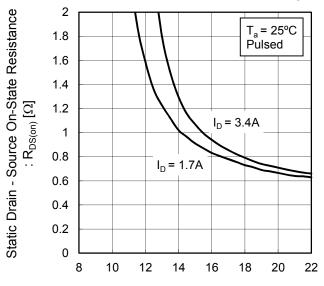
Junction Temperature :  $T_i$  [°C]

Fig.11 Transconductance vs. Drain Current



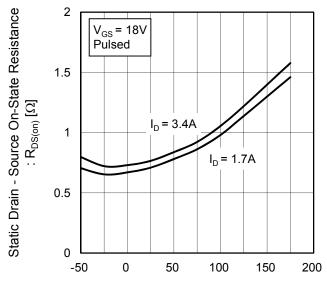
Drain Current : I<sub>D</sub> [A]

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



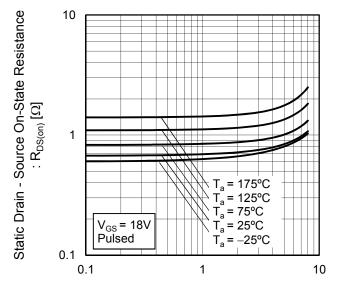
Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.13 Static Drain - Source On - State
Resistance vs. Junction Temperature



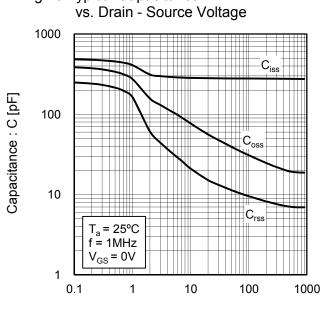
Junction Temperature : T<sub>i</sub> [°C]

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



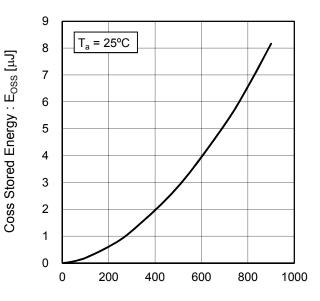
Drain Current : I<sub>D</sub> [A]

Fig.15 Typical Capacitance



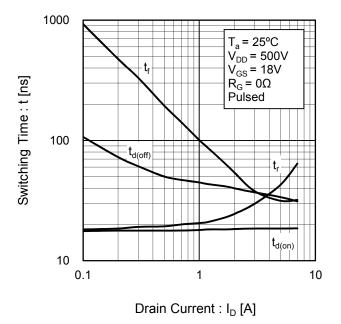
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.16 Coss Stored Energy



Drain - Source Voltage : V<sub>DS</sub> [V]

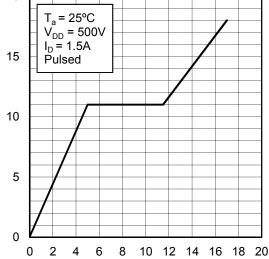
Fig.17 Switching Characteristics



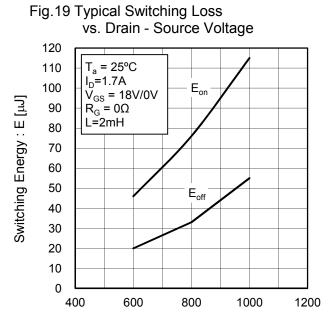
Gate - Source Voltage :  $V_{GS}$  [V]

20 T = 25°C

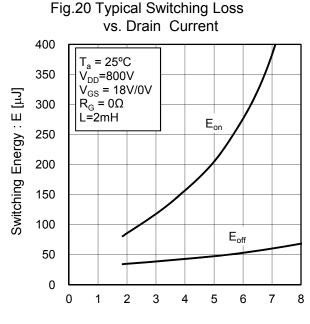
Fig.18 Dynamic Input Characteristics



Total Gate Charge : Q<sub>q</sub> [nC]

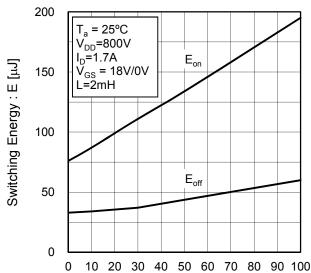


Drain - Source Voltage : V<sub>DS</sub> [V]



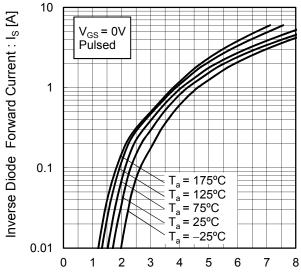
Drain Current : I<sub>D</sub> [A]

Fig.21 Typical Switching Loss vs. External Gate Resistance



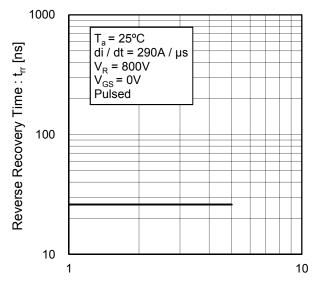
External Gate Resistance :  $R_G [\Omega]$ 

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage :  $V_{SD}$  [V]

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I<sub>S</sub> [A]

## Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

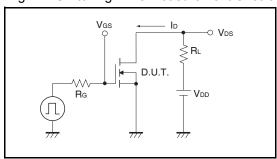


Fig.2-1 Gate Charge Measurement Circuit

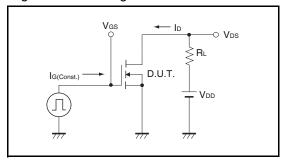


Fig.3-1 Switching Energy Measurement Circuit

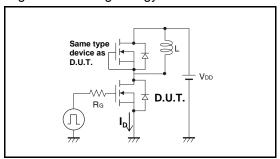


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

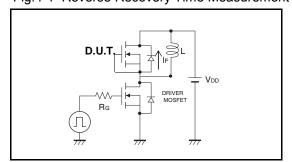


Fig.1-2 Switching Waveforms

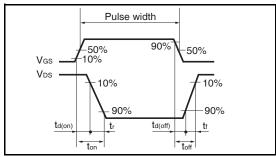


Fig.2-2 Gate Charge Waveform

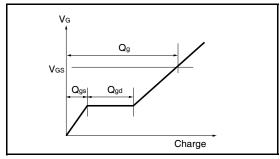
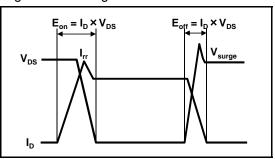
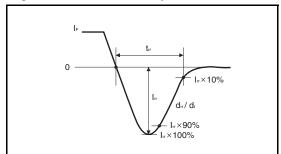


Fig.3-2 Switching Waveforms





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